

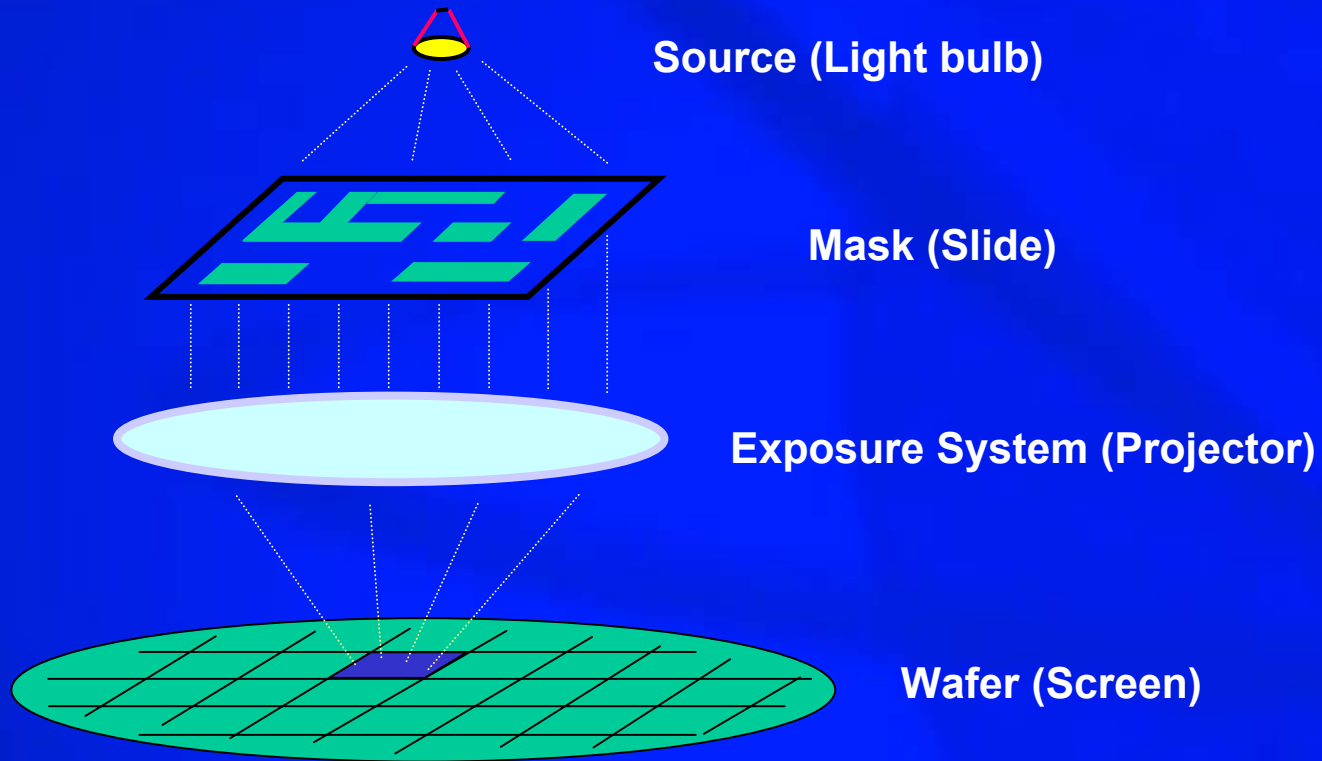
# **Mask Making Tutorial**

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Intel Mask Operation**

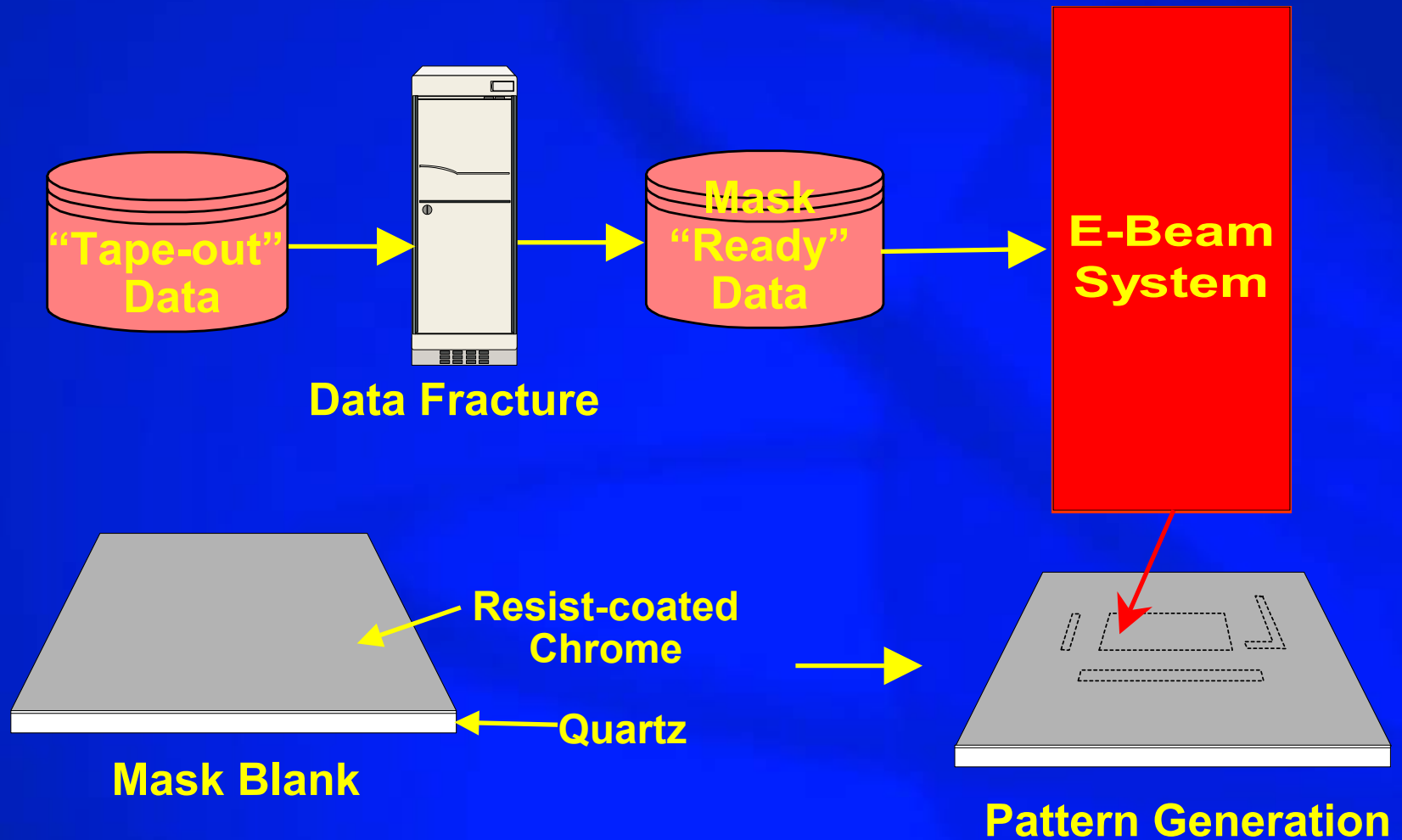
# Outline

- What Is a Mask and How Is It Used in Semiconductor Lithography?
- What Are the Main Mask-making Steps?
- Why Is Lithography So Difficult?
- Mask Making Eras
- Printing Features With Low  $k_1$  Lithography
- The Mask Maker's Low  $k_1$  Burden
- The Technology Treadmill
- Why Are Mask Costs Increasing So Significantly?
- Some Mask Making Metrics

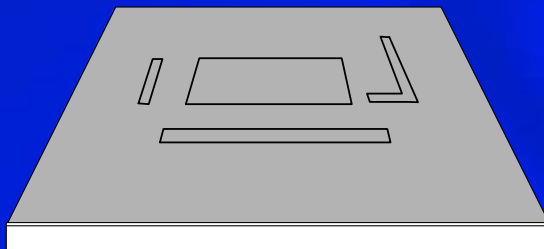
# What Is a Mask and How Is It Used in Semiconductor Lithography?



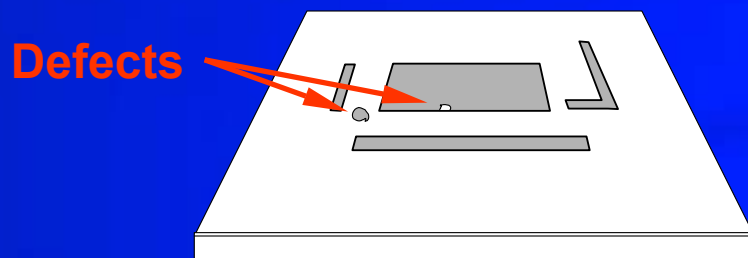
# Main Mask-Making Steps



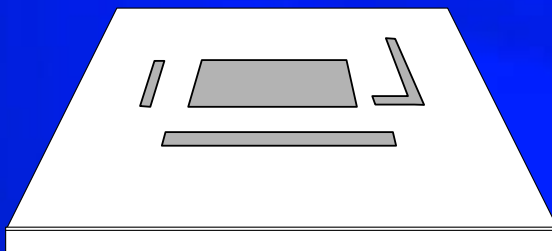
# Main Mask-Making Steps



**Develop**



**Etch**



**Inspect and Repair**

# Why is Lithography So Difficult?

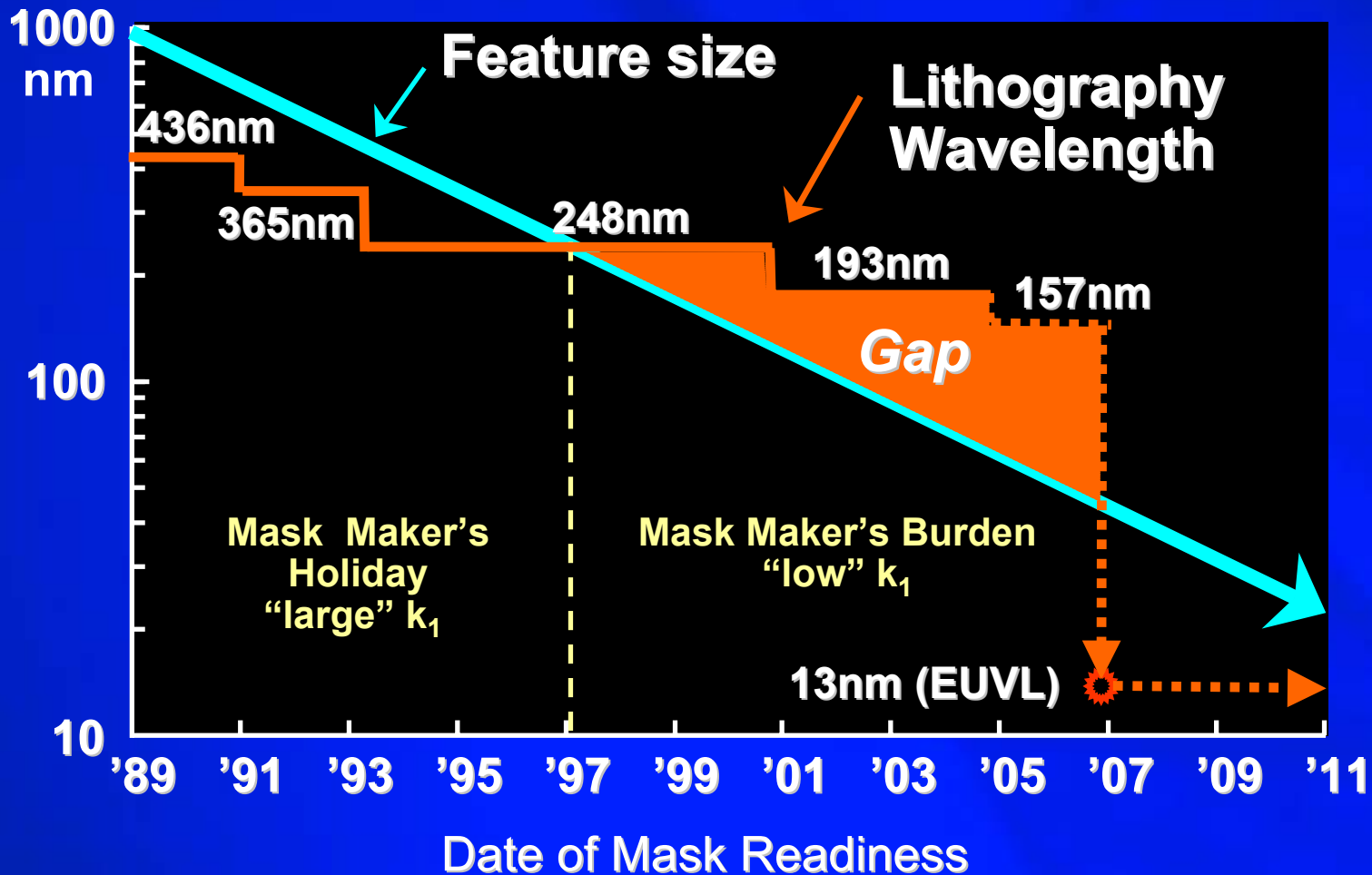
- Three lithography “knobs” to twist
  - Exposure wavelength ( $\lambda$ )—the smaller the better
  - Lens size (Numerical Aperture—NA)—the larger the better
  - Process complexity factor ( $k_1$ )

$$\text{Feature size} = k_1 \otimes \text{wavelength} \div \text{lens size}$$

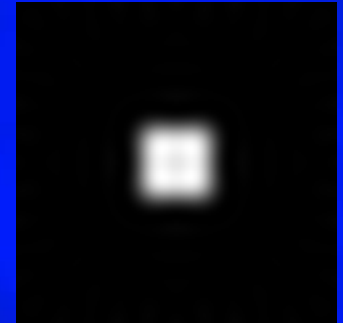
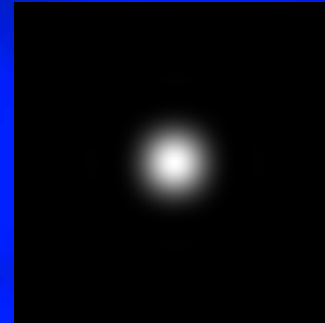
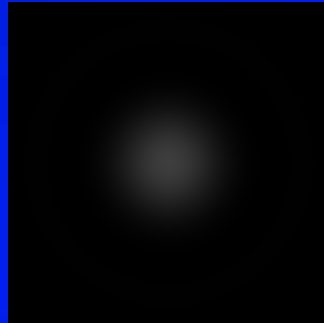
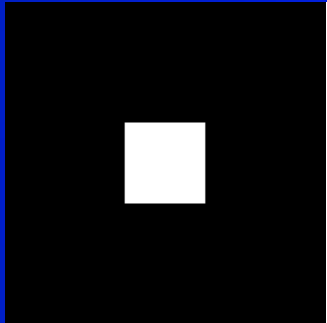
- » A measure of lithography aggressiveness
- » Smaller means the ability to print smaller features
- Wavelength scaling has not kept up with the rate of feature size scaling
  - Time and cost to engineer new lasers and exposure systems
- Lens size can only grow so large
  - Size and cost of Lenses; maximum lens size:  $NA = 1$
- Making the process complexity factor smaller has been the area of primary effort

**The burden of doing this falls primarily on the mask maker!**

# Mask Making Eras



# Printing Features With Low $k_1$ Lithography



"small" lens

"medium" lens

"large" lens

What we ask for



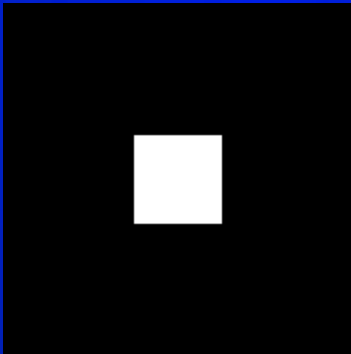
What we get



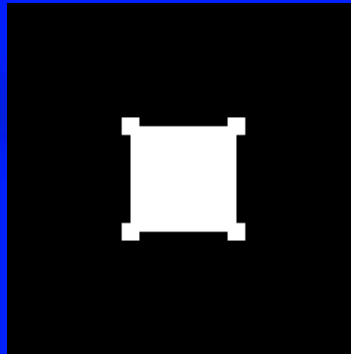
# The Mask Maker's Low $k_1$ Burden

- What we get is not what we asked for
- **Solution: Ask for something different**
  - This is the idea behind RET (resolution enhancement technology)
- It takes various forms
  - Embellishments (Optical Proximity Correction—OPC features)
  - 3-D structures (Phase-shift Masks)

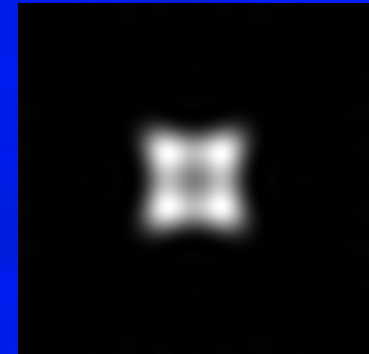
## Example of OPC



Want this

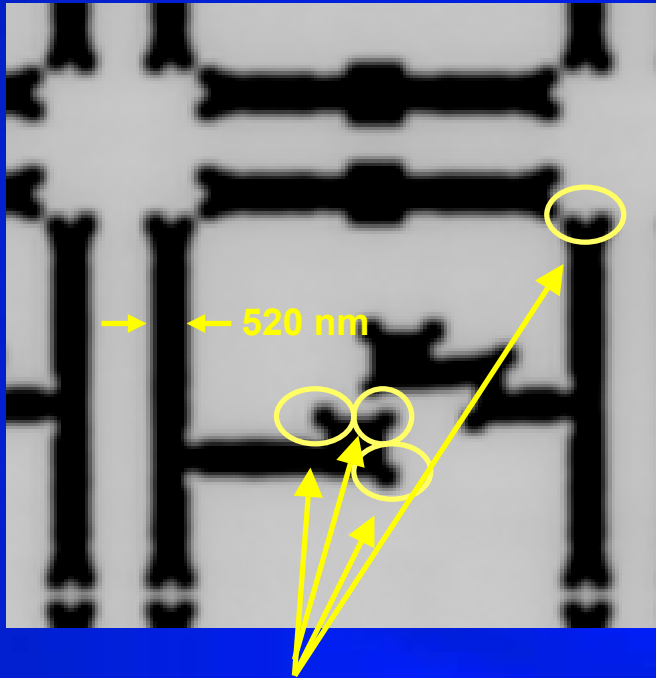


Ask for this  
On the mask



Get this  
On the wafer

# The Mask Maker's Low $k_1$ Burden—A Real Example



RET “embellishments” must be fully resolved on the mask

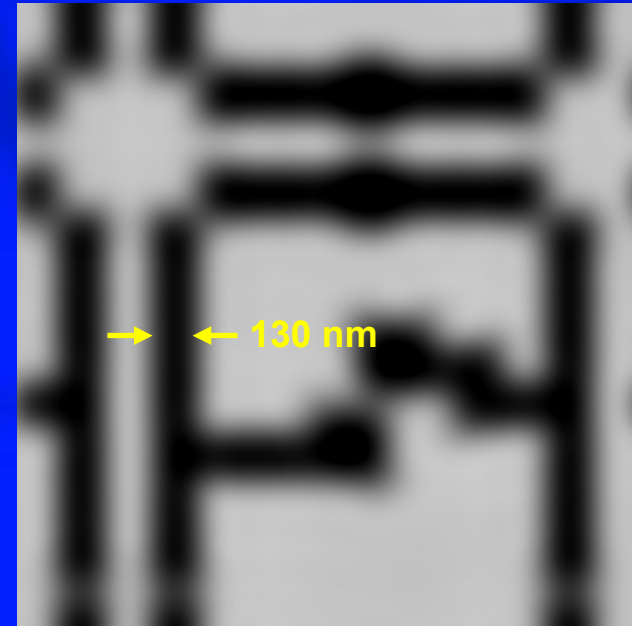
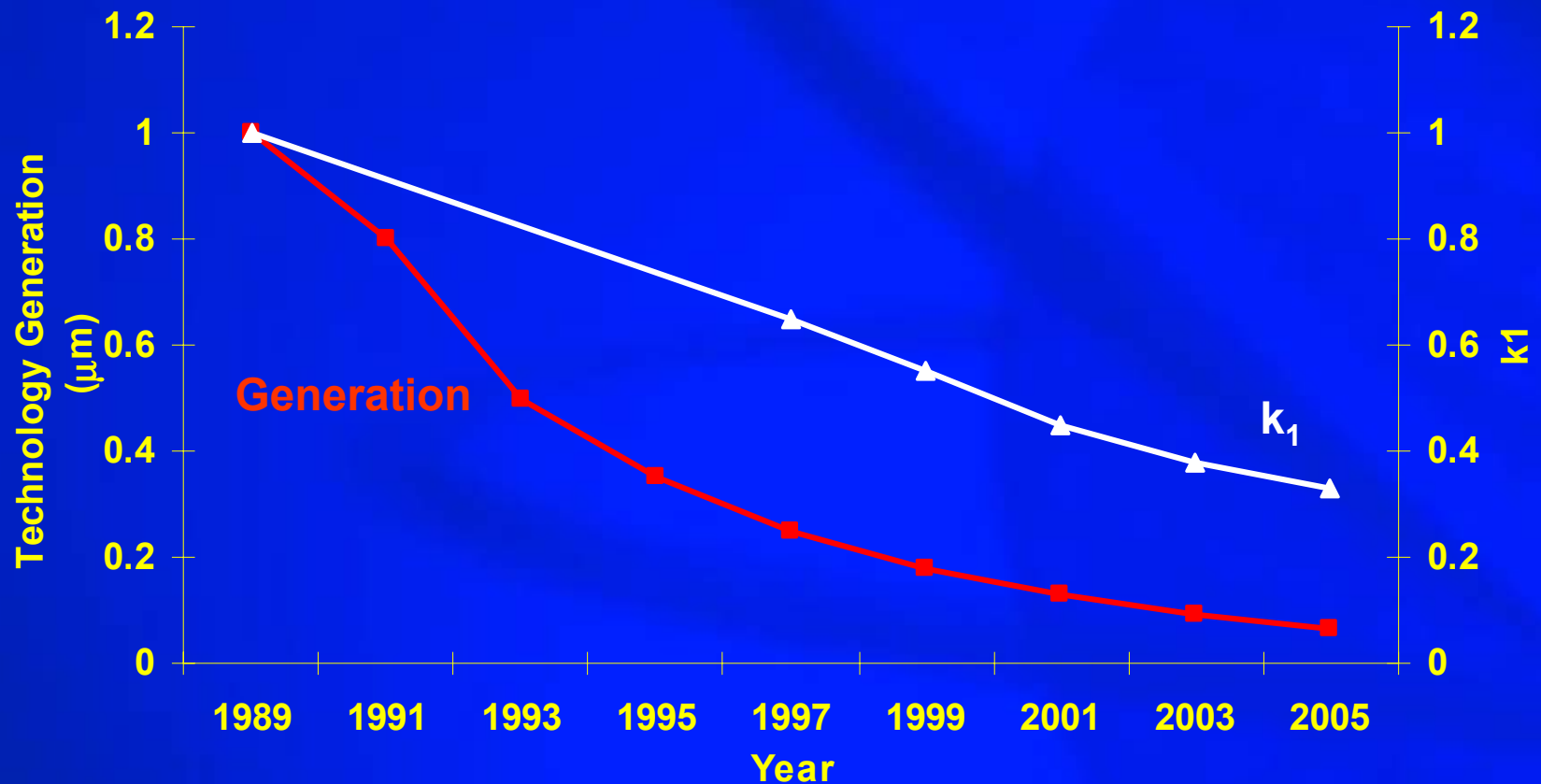


Image on the wafer

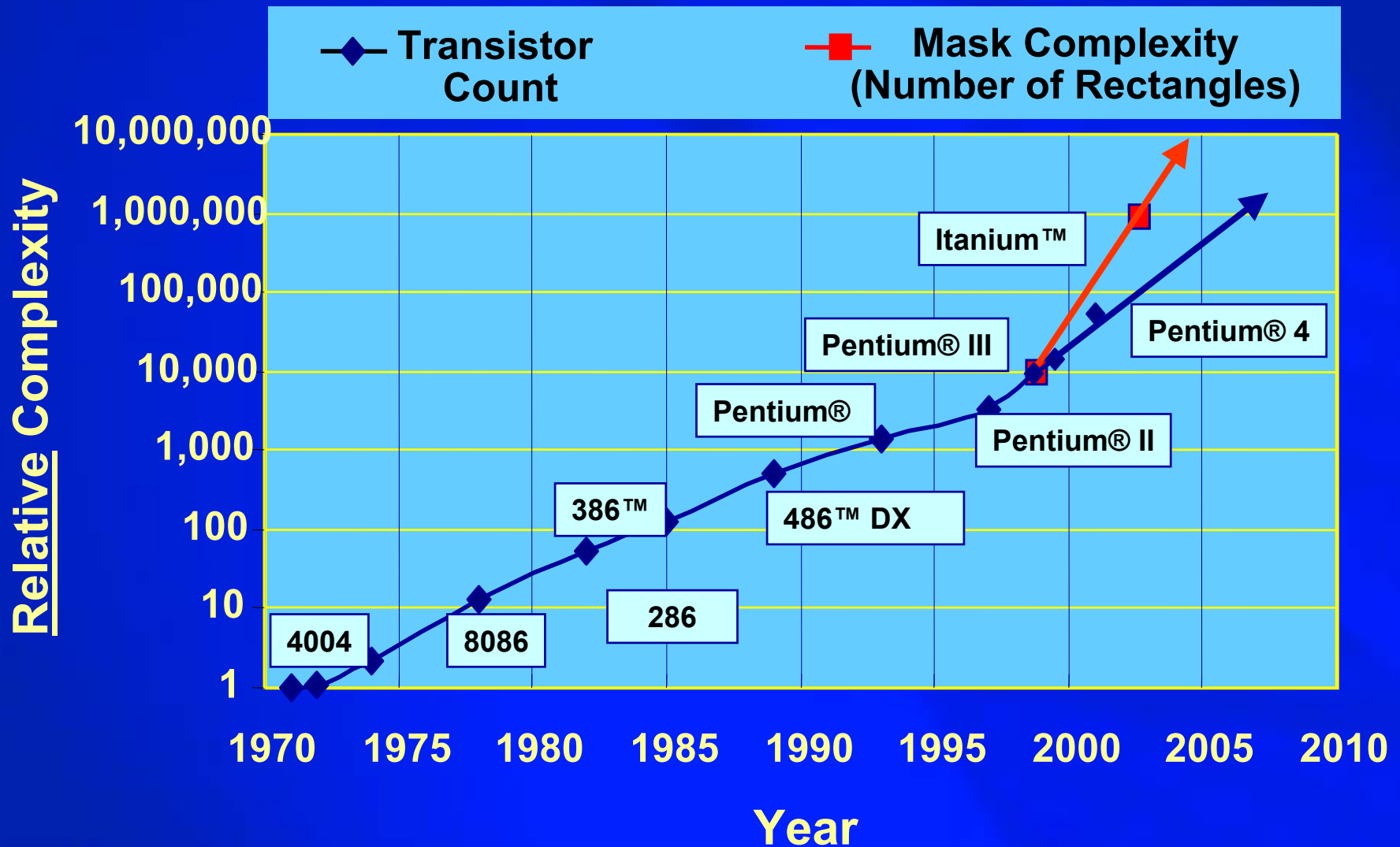
NOT OUT of FOCUS!

# The Technology Treadmill

## Technology Generation and $k_1$ Value



# Why Are Mask Costs Increasing So Significantly?



# Some Mask-Making Metrics and Comparisons

## •Pixels:

- On a 90 nm technology node mask: 1,000,000,000,000
- In a high quality digital photo: 4,000,000

## •Defects:

- Size that must be found and repaired 0.1 micron
- Number of such defects allowed: 0
- Size ratio: defect to the mask area: size of a basketball  
area of California

## •Data

- Typical number of mask layers for 90 nm generation logic product: 22—25
- Total file size needed to specify all these layers: 200 GB
- Time to transmit (design site to mask shop) using T1 line (1.4 MB/sec): ~1.5 days
- Time using T3 line (40 MB/sec): ~1.5 hours

## •Cost

- Cost to lease a T3 line: \$70K/month
- Capital cost to build a 90 nm node capable mask shop (capacity of 200 sets/year @50-70% yield): \$200-250M
- Yearly cost to operate such a shop: \$60-100M
- Cost to make a 90 nm node mask set (depreciation, labor, etc): ~\$800K-1.3M